

WHAT IS CLAIMED IS:

1. A semiconductor device comprising a semiconductor substrate, and aluminum conductors formed on a side of a main face of the substrate which aluminum conductors comprises aluminum as main constituent thereof, said aluminum conductors containing copper and nickel.
2. A semiconductor device according to claim 1, wherein said aluminum conductors has at least one area in which conductor spacing is not more than 0.4 μm .
3. A semiconductor device according to claim 2, wherein the content of nickel contained in said aluminum conductors is not less than 0.02 at.% but not more than 1 at.%.
4. A semiconductor device comprising a semiconductor substrate, and aluminum conductors formed on a side of a main face of the substrate which aluminum conductors comprise aluminum as main constituent thereof, a film adjacent to said aluminum conductors which adjacent film comprises titanium or titanium nitride as main constituent thereof, said aluminum conductors containing copper and nickel.
5. A semiconductor device comprising a semiconductor substrate, and aluminum conductors formed on a side of a main face of the substrate which aluminum conductors comprise aluminum as main constituent thereof, said aluminum conductors containing copper and silicon.
6. A semiconductor device according to claim 5,

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wherein said aluminum conductors has at least one area in which conductor spacing is not more than 0.4 μm .

7. A semiconductor device according to claim 6, wherein the content of silicon contained in said aluminum conductors is not less than 0.05 at.% but not more than 0.4 at.%.

8. A semiconductor device comprising a semiconductor substrate, and aluminum conductors formed on a side of a main face of the substrate which aluminum conductors comprise aluminum as main constituent thereof, a film adjacent to said aluminum conductors which adjacent film comprises titanium or titanium nitride as main constituent thereof, said aluminum conductors containing copper and silicon.

9. A semiconductor device comprising a semiconductor substrate, and aluminum conductors formed on a side of a main face of the substrate which aluminum conductors comprises aluminum as main constituent thereof, said aluminum conductors having at least one area in which conductor spacing is not more than 0.4 μm , a film adjacent to said aluminum conductors which adjacent film comprises one kind selected from the group consisting of ruthenium, platinum and iridium as main constituent thereof, said aluminum conductors containing copper.

10. A semiconductor device according to claim 9, wherein said aluminum conductors contain nickel not less than 0.02 at.% but not more than 1 at.%.

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11. ~~A~~ A semiconductor device according to claim 9, wherein said aluminum conductors contain silicon not less than 0.05 at.% but not more than 0.4 at.%.

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